



Standard Rectifier Module

PHASE OUT

3~ Rectifier Bridge

3~

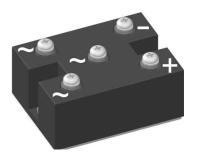
Phase out

Rectifier $V_{RRM} = 1400 \text{ V}$ 120 A

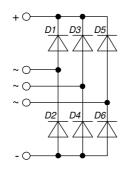
 $I_{FSM} = 1500 A$

Part number

VUO105-14NO7







Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Diode for main rectification
- For three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: PWS-C

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Easy to mount with two screws
- Base plate: Copper internally DCB isolated
- Advanced power cycling

Recommended replacement: VUO105-16NO7

Terms and Conditions of Usage

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office

Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

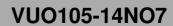
to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747 and per semiconductor unless otherwise specified

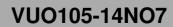
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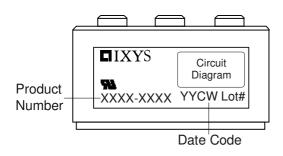
Rectifier				1	Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit	
V _{RSM}	max. non-repetitive reverse bloc	cking voltage	$T_{VJ} = 25^{\circ}C$			1500	V	
V _{RRM}	max. repetitive reverse blocking	voltage	$T_{VJ} = 25^{\circ}C$			1400	V	
I _R	reverse current	V _R = 1400 V	$T_{VJ} = 25^{\circ}C$			100	μΑ	
		$V_R = 1400 V$	$T_{VJ} = 150$ °C			2	mΑ	
V _F	forward voltage drop	I _F = 40 A	$T_{VJ} = 25^{\circ}C$			1.09	V	
		$I_F = 120 A$				1.38	٧	
		$I_F = 40 \text{ A}$	T _{VJ} = 125°C			1.00	٧	
		$I_F = 120 \text{ A}$				1.36	٧	
I DAV	bridge output current	T _C = 105°C	T _{vJ} = 150°C			120	Α	
		rectangular d = ⅓						
V _{F0}	threshold voltage		T _{vJ} = 150°C			0.78	V	
r _F	slope resistance } for power	loss calculation only				4.8	mΩ	
R _{thJC}	thermal resistance junction to ca	ase				0.8	K/W	
R _{thCH}	thermal resistance case to heats	sink			0.30		K/W	
P _{tot}	total power dissipation		$T_{C} = 25^{\circ}C$			155	W	
I _{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			1.50	kA	
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			1.62	kA	
		t = 10 ms; (50 Hz), sine	T _{vJ} = 150°C			1.28	kA	
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			1.38	kA	
l²t	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			11.3	kA2s	
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			10.9	kA2s	
		t = 10 ms; (50 Hz), sine	T _{vJ} = 150°C			8.13	kA2s	
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			7.87	kA2s	
CJ	junction capacitance	$V_{R} = 400 \text{ V}; f = 1 \text{ MHz}$	$T_{VJ} = 25^{\circ}C$		58		pF	

PHASE OUT





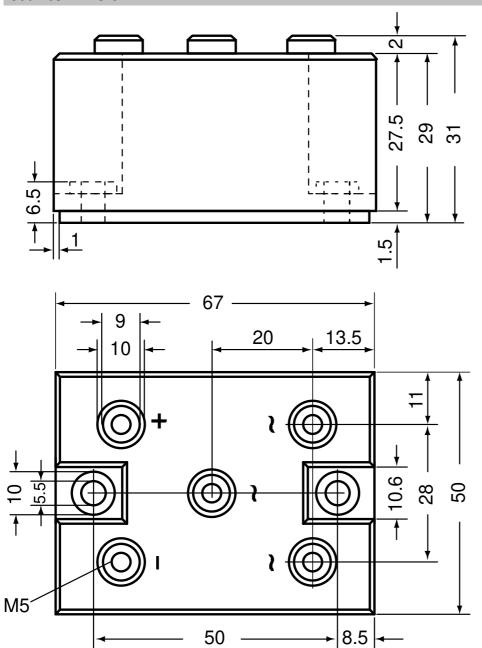
Package PWS-C			Ratings				
Symbol	Definition	Conditions		min.	typ.	max.	Unit
IRMS	RMS current	per terminal				150	Α
T _{VJ}	virtual junction temperature			-40		150	°C
T _{op}	operation temperature			-40		125	°C
T _{stg}	storage temperature			-40		125	°C
Weight					250		g
M _D	mounting torque			4.25		5.75	Nm
$\mathbf{M}_{_{T}}$	terminal torque			4.25		5.75	Nm
d _{Spp/App}	creenage distance on surface	e striking distance through air	terminal to terminal	26.0			mm
$d_{Spb/Apb}$	creepage distance on surfac	e striking distance through an	terminal to backside	14.0			mm
V _{ISOL}	isolation voltage	t = 1 second	50/00 II	3000			٧
.002		$t = 1 \text{ minute}$ 50/60 Hz, RMS; IsoL $\leq 1 \text{ r}$	50/60 Hz, RMS; IISOL ≤ 1 mA	2500			٧

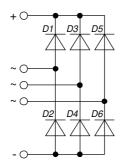


Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VUO105-14NO7	VUO105-14NO7	Box	10	456721

Equivalent Circuits for Simulation			* on die level	$T_{VJ} = 150 ^{\circ}\text{C}$
$I \rightarrow V_0$)—[R ₀]-	Rectifier		
V _{0 max}	threshold voltage	0.78		V
$R_{0 \; max}$	slope resistance *	3.6		$m\Omega$

Outlines PWS-C





Rectifier

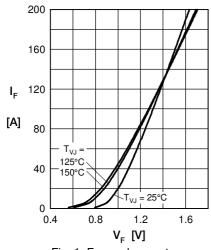


Fig. 1 Forward current versus voltage drop per diode

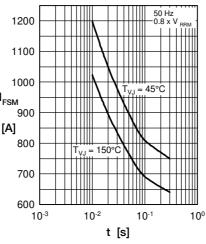


Fig. 2 Surge overload current vs. time per diode

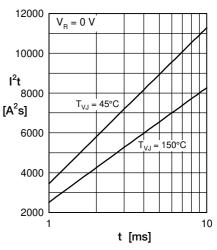


Fig. 3 I²t versus time per diode

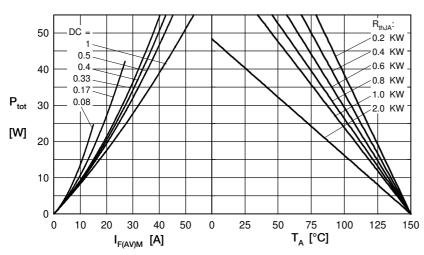


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

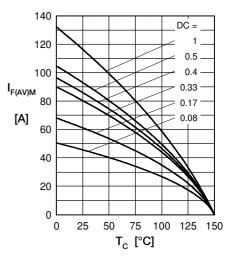


Fig. 5 Max. forward current vs. case temperature per diode

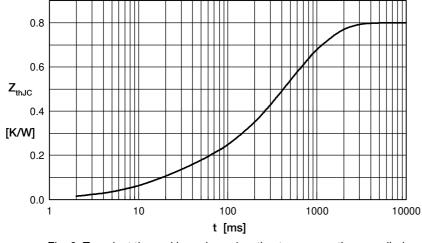


Fig. 6 Transient thermal impedance junction to case vs. time per diode

Constants for \mathbf{Z}_{thJC} calculation:

i	R_{th} (K/W)	t _i (s)
1	0.100	0.020
2	0.014	0.010
3	0.192	0.225
4	0.281	0.800
5	0.213	0.580